

SOT-23 Plastic-Encapsulate Transistors

MMBT5401 TRANSISTOR (PNP)

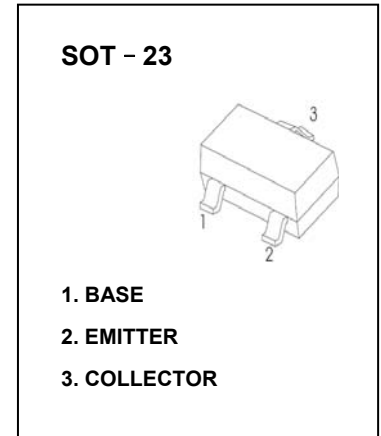
FEATURES

- Complementary to MMBT5551
- Ideal for Medium Power Amplification and Switching

MARKING: 2L

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.6	A
P_C	Collector Power Dissipation	0.3	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	416	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=-1\text{mA}, I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-120\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	80			
	$h_{FE(2)}^*$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	100		300	
	$h_{FE(3)}^*$	$V_{CE}=-5\text{V}, I_C=-50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)1}^*$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.2	V
	$V_{CE(sat)2}^*$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)1}^*$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-1	V
	$V_{BE(sat)2}^*$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=30\text{MHz}$	100			MHz

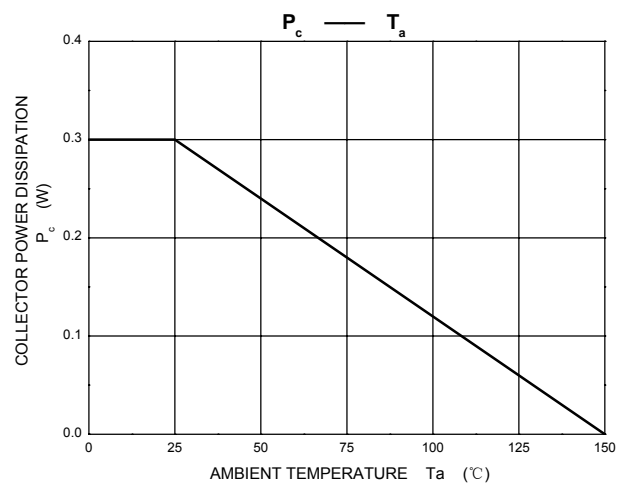
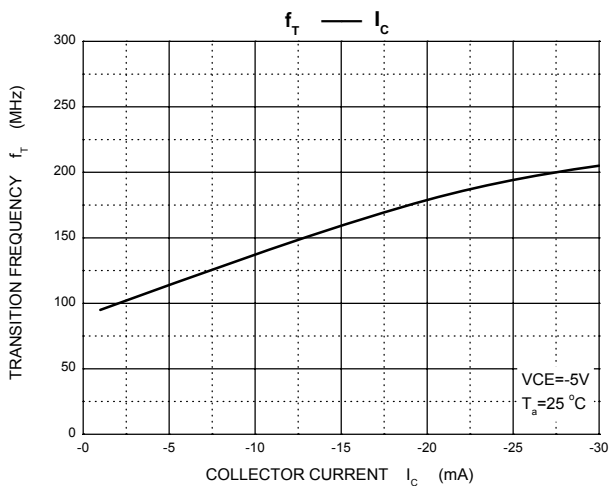
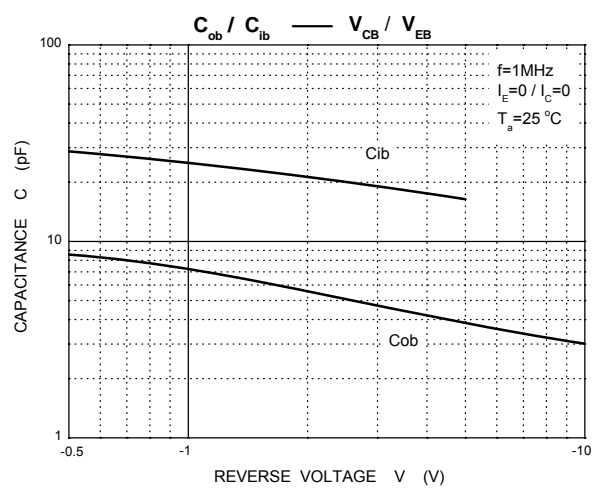
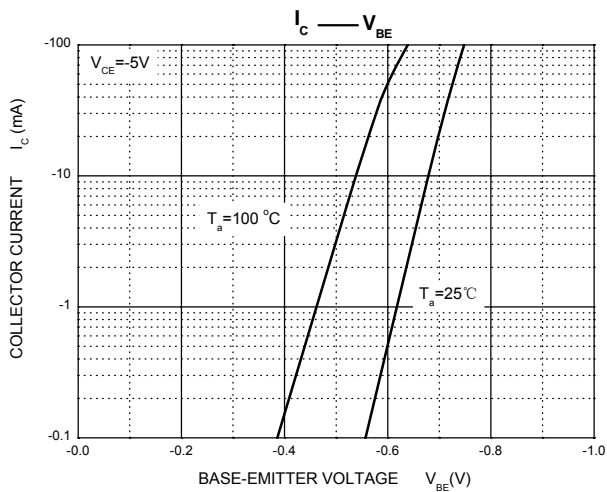
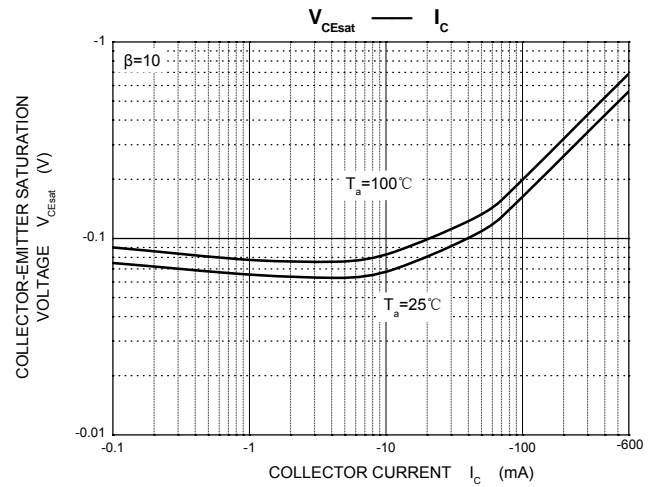
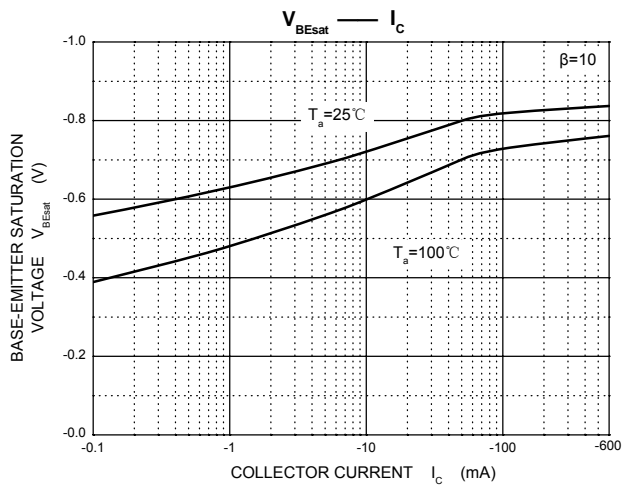
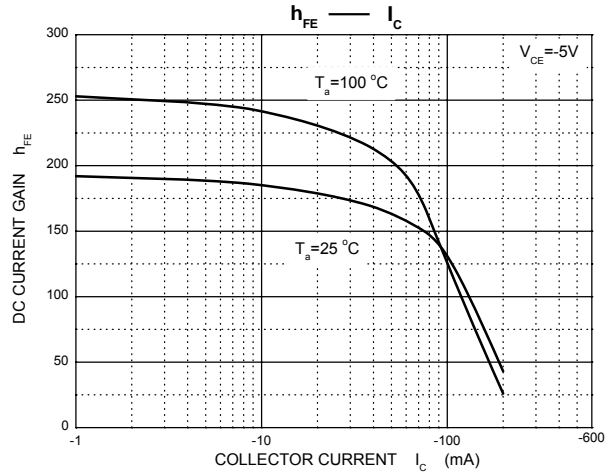
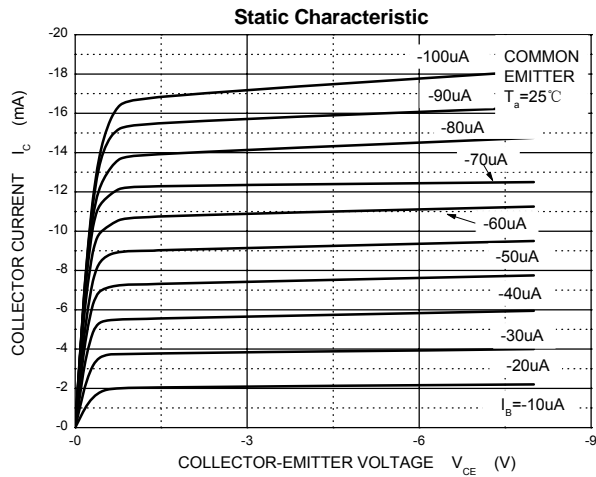
*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycles $\leq 2.0\%$.

CLASSIFICATION OF $h_{FE(2)}$

RANK	L	H
RANGE	100-200	200-300

Typical Characteristics

MMBT5401



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [Changjiang manufacturer](#):

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NJVMJD148T4G](#) [NTE123AP-10](#) [NTE153MCP](#) [NTE16](#)
[NTE195A](#) [NTE92](#) [C4460](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC2712S-GR,LF](#) [2SC5488A-TL-H](#)
[2SD2150T100R](#) [SP000011176](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC2412KT146S](#) [2SD1816S-TL-E](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#)
[MJE340](#) [US6T6TR](#) [NJL0281DG](#) [732314D](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [UMX21NTR](#) [MCH6102-TL-E](#)
[NJL0302DG](#) [2N3583](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE13](#) [NTE26](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [STX83003-AP](#)